## New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A. TELEPHONE: (973) 376-2922 (212) 227-6005

FAX: (973) 376-8960

## 2N6083

## NPN SILICON RF POWER TRANSISTORS

... designed for 12.5 Volt VHF large-signal power amplifier applications required in military and industrial equipment operating to

 Specified 12.5 Volt, 175 MHz Characteristics — Output Power = 30 W – 2N6083

Minimum Gain = 5.7 dB - 2N6083

 Balanced Emitter Construction to provide the designer with the device technology that assures ruggedness and resists transistor damage caused by load mismatch

## \*MAXIMUM RATINGS

3						
Rating	Symbol	2NG083	. Unit			
Collector-Emitter Voltage	VCEO	18				
Collector-Base Voltage	∨сво	36	Vdc			
Emitter-Base Voltage	VERO	4.0	Vdc			
Collector Current Continuous	o.	4.0	Adc			
Total Device Dissipation @ T <sub>C</sub> = 75°C(2) Derate above 25°C	PD	65 0.52	Watts W/ <sup>O</sup> C			
Storage Temperature Range	T <sub>stg</sub>	-65 to +200 °C				
Stud Torque(1)	_	6.5	in. lb.			
Stud Torque(1)	- 6.5		In. ID.			

\*Indicates JEDEC Registered Data (1) For Repeated Assembly Use 5 in. lb.

(2) These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.

\*ELECTRICAL CHARACTERISTICS (TC \* 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	. Max	Unit
OFF CHARACTERISTICS						
Collector Emitter Breakdown Voltage (IC = 100 mAdc, IB = 0)	ı	BVCEO	18	-	-	Vdc
Collector Emitter Breakdown Voltage (I <sub>C</sub> = 15 mAdc, V <sub>BE</sub> = 0)	2N6083	BVCES	36			Vdc
Emitter-Base Breakdown Voltage (IE = 5.0 mAdc, IC = 0)	2NG083	BVEBO	4.0			Vdc
Collector Cutoff Current (VCE = 15 Vdc, VBE = 0, TC = +55°C)		CES			10	mAdc
Collector Cutoff Current (VCB = 15 Vdc, IE = 0)	2NG083	СВО		-	1.0	mAdc
ON CHARACTERISTICS				,	·	
DC Current Gain (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 5.0 Vdc)		ptE	5.0	_	'	_
DYNAMIC CHARACTERISTICS				<b></b>		
Output Capacitance (VCB = 15 Vdc, IE = 0, f = 0.1 MHz)	2NG083	C <sub>ob</sub>	-	110	130	ρF
FUNCTIONAL TEST					·	
Common-Emitter Amplifier Power Gain		GPE		_		dB
(Pout = 30 W, V <sub>CC</sub> = 12.5 Vdc, f = 175 MHz)	2N6083		5.7	-	<del>-</del>	
Collector Efficiency		η		_	_	%
(P <sub>out</sub> = 30 W, V <sub>CC</sub> = 12.5 Vdc, f = 175 MHz)	2N6083		65	-	-	

